

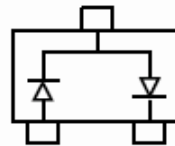
SWITCHING DIODE

BAV199

FEATURES

- This switching diode has the following features:
- Low Leakage Current Applications

Marking:52



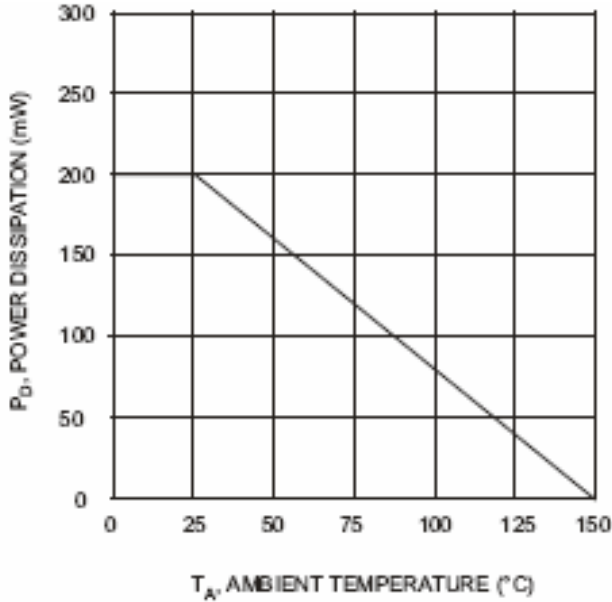
Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	70	V
DC Blocking Voltage	V _R	70	V
Forward Continuous Current	I _{FM}	500	mA
Average Rectified Output Current	I _O	215	mA
Power Dissipation	P _D	200	mW
Junction temperature	T _J	125	°C
Storage temperature range	T _{STG}	-55-125	°C

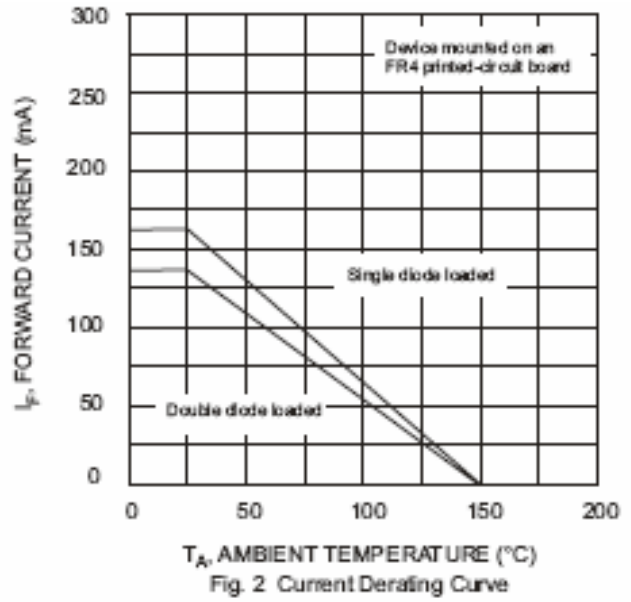
ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR)	I _R = 100µA	70		V
Reverse voltage leakage current	I _R	V _R =70V		5	nA
Forward voltage	V _F	I _F =1mA I _F =10mA I _F =50mA I _F =150mA		900 1000 1100 1250	mV
Diode capacitance	C _D	V _R =0, f=1MHz		2	pF
Reverse recovery time	t _{rr}	I _F = I _R = 10mA		3	µS

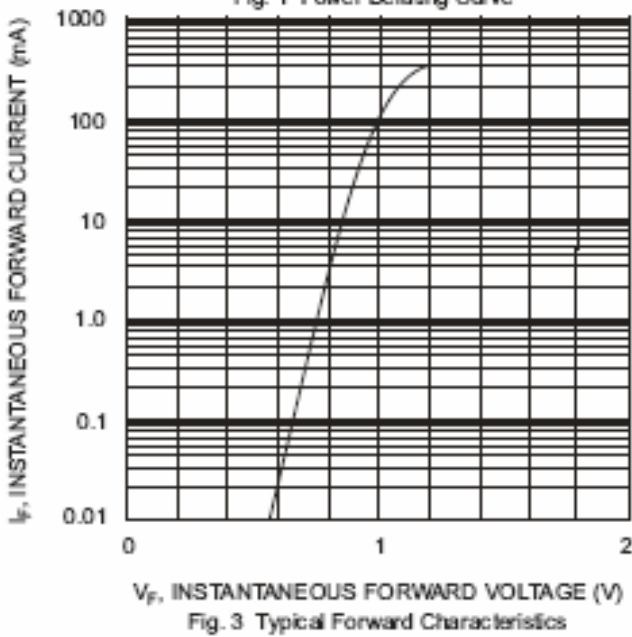
BAV199 Typical Characteristics



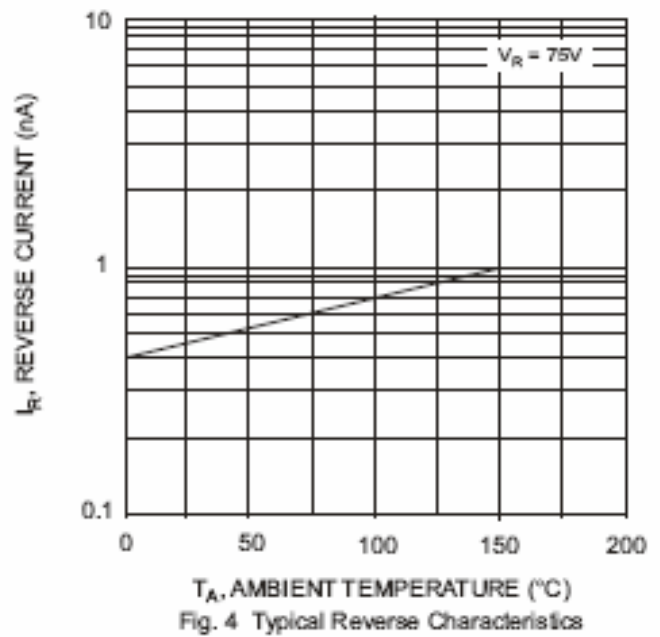
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1 Power Derating Curve



T_A , AMBIENT TEMPERATURE (°C)
Fig. 2 Current Derating Curve



V_F , INSTANTANEOUS FORWARD VOLTAGE (V)
Fig. 3 Typical Forward Characteristics



T_A , AMBIENT TEMPERATURE (°C)
Fig. 4 Typical Reverse Characteristics